

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of Ming-Dou KER et al.

Serial Number: 09/773,754

Group Art Unit: 2826

Filed: February 2, 2001

Examiner: SEFER, A

For: ESD PROTECTION DESIGN WITH TURN-ON RESTRAINING METHOD AND STRUCTURES

AMENDMENT

Director of Patents and Trademarks
Washington, D.C. 20231

March 12, 2002

Sir:

In response to the Office Action dated December 3, 2001 (hereinafter outstanding Action), the applicants respectfully request that the present application be amended as follows, and that the rejection of record be reconsidered in view of the amendments and remarks.

IN THE CLAIMS:

Please amend claims 1, 2, 4, 7-9, 11 and 14-18 by way of replacement. A marked-up version of the amended claims is enclosed in the Appendix.

1. (Amended) A semiconductor structure for electrostatic discharge (ESD) protection
- A1 of a metal-oxide semiconductor (MOS) integrated circuit comprising:
- a substrate of a first conductivity type forming a base for said semiconductor structure;
 - a first region of a second conductivity type within said substrate for forming a drain of a first MOS transistor;